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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21274sdfp-x6

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.

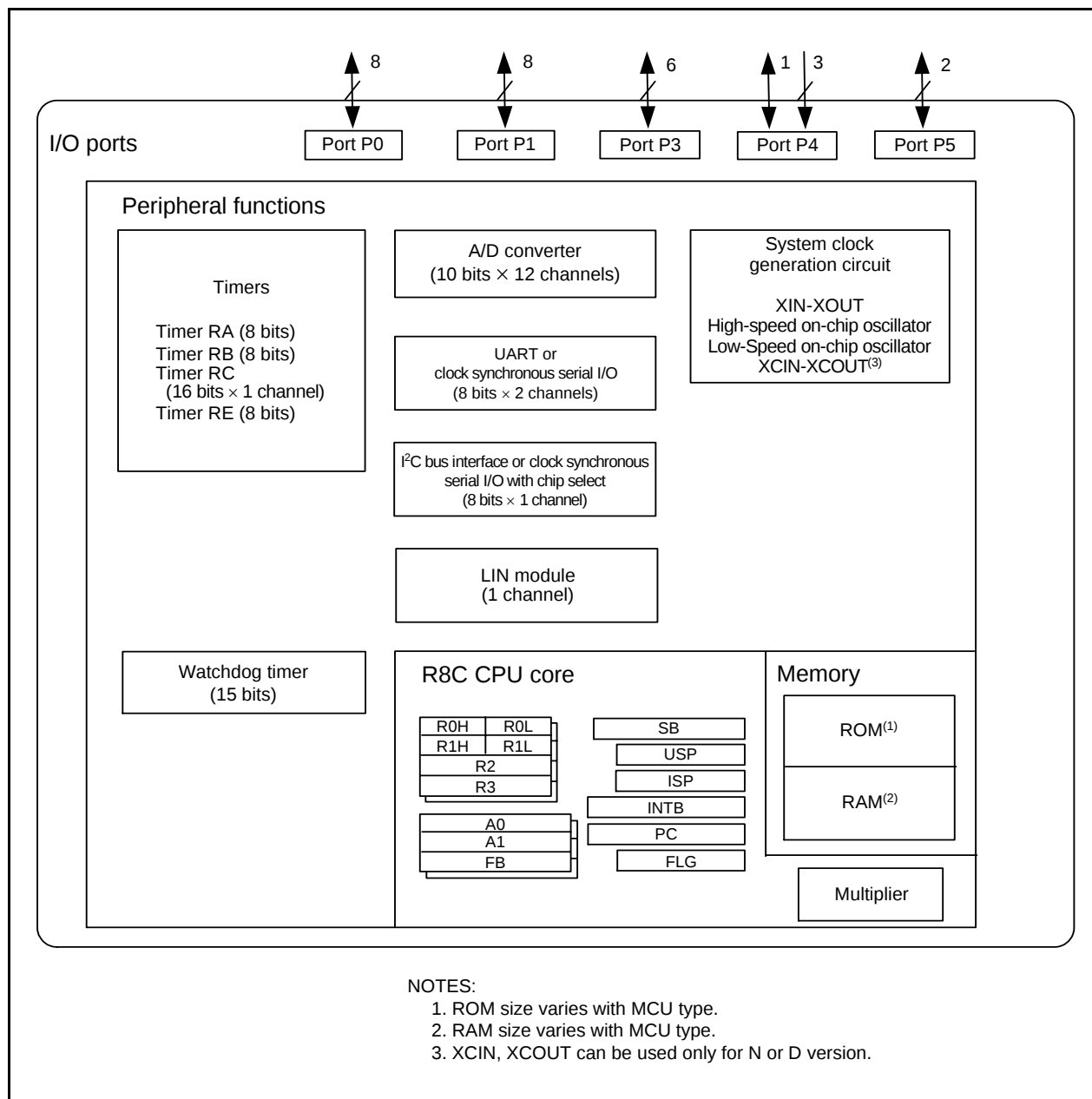


Figure 1.1 Block Diagram

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 to be used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

3. Memory

3.1 R8C/26 Group

Figure 3.1 is a Memory Map of R8C/26 Group. The R8C/26 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

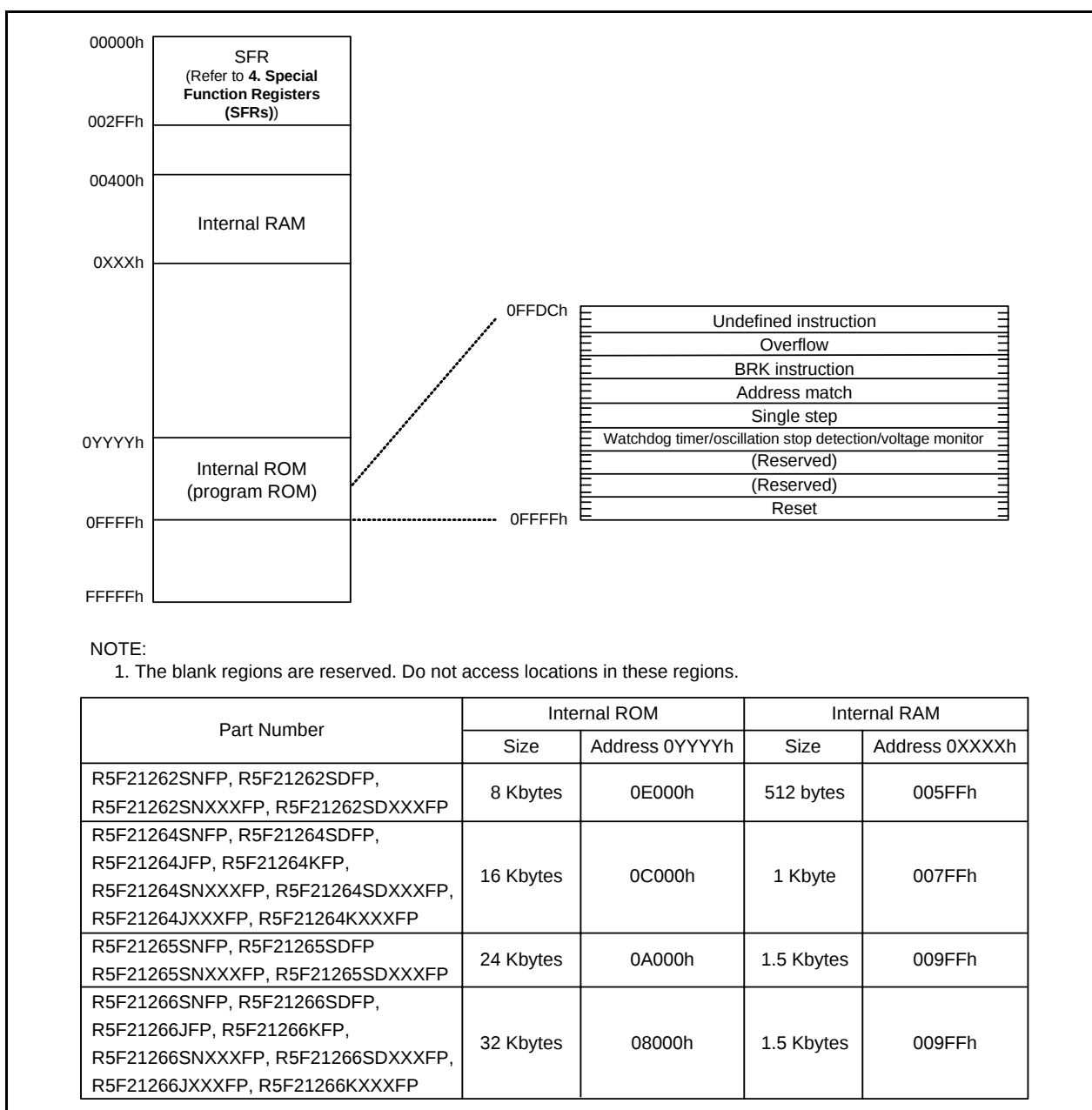


Figure 3.1 Memory Map of R8C/26 Group

3.2 R8C/27 Group

Figure 3.2 is a Memory Map of R8C/27 Group. The R8C/27 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

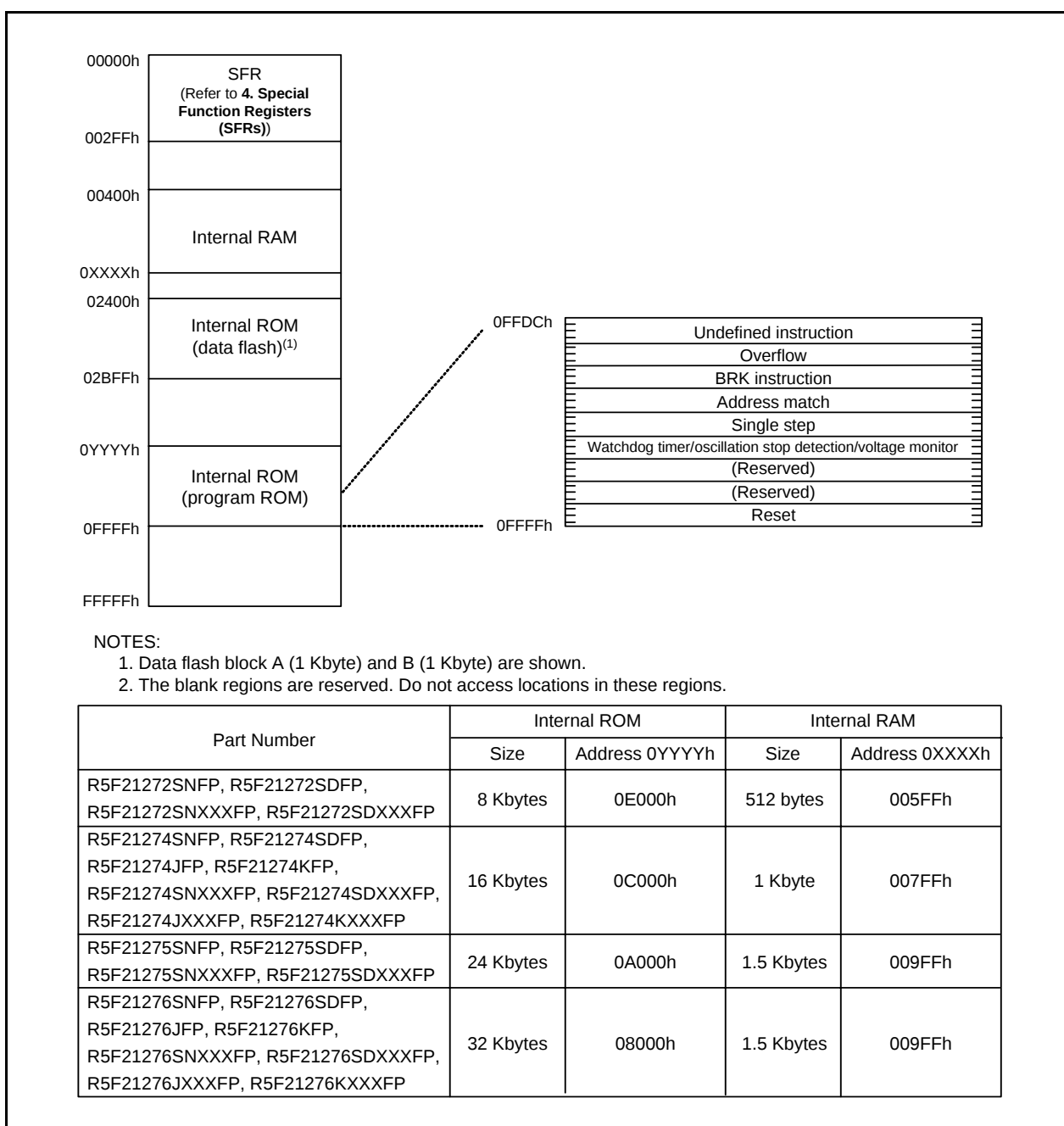


Figure 3.2 Memory Map of R8C/27 Group

Table 4.3 SFR Information (3)⁽¹⁾

Address	Register	Symbol	After reset
0080h			
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h			
0089h			
008Ah			
008Bh			
008Ch			
008Dh			
008Eh			
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
00A9h	UART1 Bit Rate Register	U1BRG	XXh
00AAh	UART1 Transmit Buffer Register	U1TB	XXh
00ABh			XXh
00ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
00ADh	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
00AEh	UART1 Receive Buffer Register	U1RB	XXh
00AFh			XXh
00B0h			
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h	SS Control Register H / IIC bus Control Register 1 ⁽²⁾	SSCRH / ICCR1	00h
00B9h	SS Control Register L / IIC bus Control Register 2 ⁽²⁾	SSCRL / ICCR2	01111101b
00BAh	SS Mode Register / IIC bus Mode Register ⁽²⁾	SSMR / ICMR	00011000b
00BBh	SS Enable Register / IIC bus Interrupt Enable Register ⁽²⁾	SSER / ICIER	00h
00BCh	SS Status Register / IIC bus Status Register ⁽²⁾	SSSR / ICSR	00h / 0000X000b
00BDh	SS Mode Register 2 / Slave Address Register ⁽²⁾	SSMR2 / SAR	00h
00BEh	SS Transmit Data Register / IIC bus Transmit Data Register ⁽²⁾	SSTDR / ICDRT	FFh
00BFh	SS Receive Data Register / IIC bus Receive Data Register ⁽²⁾	SSRDR / ICDRR	FFh

X: Undefined

NOTES:

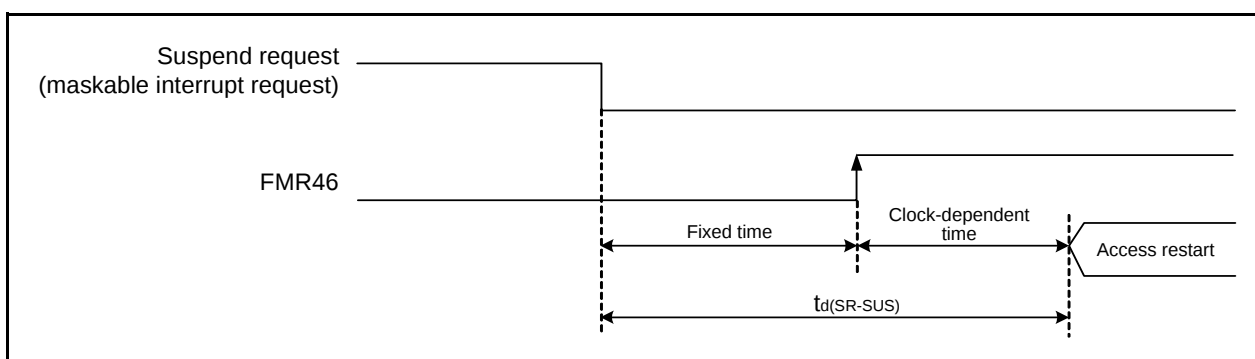
1. The blank regions are reserved. Do not access locations in these regions.
2. Selected by the IICSEL bit in the PMR register.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics⁽⁴⁾

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	50	400	μs
—	Byte program time (program/erase endurance > 1,000 times)		—	65	—	μs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	9	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	97 + CPU clock × 6 cycles	μs
—	Interval from erase start/restart until following suspend request		650	—	—	μs
—	Interval from program start/restart until following suspend request		0	—	—	ns
—	Time from suspend until program/erase restart		—	—	3 + CPU clock × 4 cycles	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		2.2	—	5.5	V
—	Program, erase temperature		-20 ⁽⁸⁾	—	85	°C
—	Data hold time ⁽⁹⁾	Ambient temperature = 55°C	20	—	—	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

**Figure 5.2 Time delay until Suspend****Table 5.6 Voltage Detection 0 Circuit Electrical Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det0}	Voltage detection level		2.2	2.3	2.4	V
—	Voltage detection circuit self power consumption	VCA25 = 1, V _{CC} = 5.0 V	—	0.9	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽²⁾		—	—	300	μs
V _{ccmin}	MCU operating voltage minimum value		2.2	—	—	V

NOTES:

1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.7 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det1}	Voltage detection level ⁽⁴⁾		2.70	2.85	3.00	V
—	Voltage monitor 1 interrupt request generation time ⁽²⁾		—	40	—	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, V _{CC} = 5.0 V	—	0.6	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

NOTES:

1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.

Table 5.8 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det2}	Voltage detection level		3.3	3.6	3.9	V
—	Voltage monitor 2 interrupt request generation time ⁽²⁾		—	40	—	μs
—	Voltage detection circuit self power consumption	VCA27 = 1, V _{CC} = 5.0 V	—	0.6	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

NOTES:

1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.9 Power-on Reset Circuit, Voltage Monitor 0 Reset Electrical Characteristics⁽³⁾

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{por1}	Power-on reset valid voltage ⁽⁴⁾		–	–	0.1	V
V _{por2}	Power-on reset or voltage monitor 0 reset valid voltage		0	–	V _{det0}	V
t _{rth}	External power V _{CC} rise gradient ⁽²⁾		20	–	–	mV/msec

NOTES:

1. The measurement condition is T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. This condition (external power V_{CC} rise gradient) does not apply if V_{CC} ≥ 1.0 V.
3. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVD0ON bit in the OFS register to 0, the VW0C0 and VW0C6 bits in the VW0C register to 1 respectively, and the VCA25 bit in the VCA2 register to 1.
4. t_{w(por1)} indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain t_{w(por1)} for 30 s or more if -20°C ≤ T_{opr} ≤ 85°C, maintain t_{w(por1)} for 3,000 s or more if -40°C ≤ T_{opr} < -20°C.

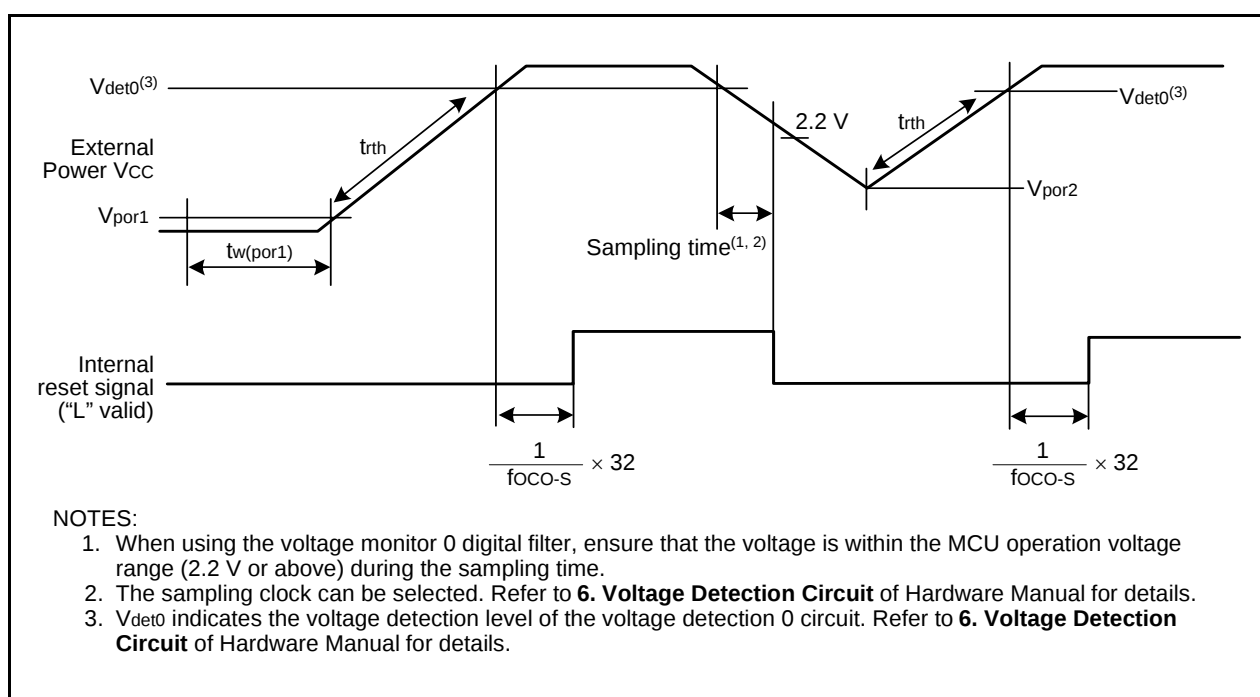
**Figure 5.3 Reset Circuit Electrical Characteristics**

Table 5.13 Timing Requirements of Clock Synchronous Serial I/O with Chip Select⁽¹⁾

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
tsucyc	SSCK clock cycle time			4	–	–	tcyc ⁽²⁾
t _{HI}	SSCK clock "H" width			0.4	–	0.6	tsucyc
t _{LO}	SSCK clock "L" width			0.4	–	0.6	tsucyc
trise	SSCK clock rising time	Master		–	–	1	tcyc ⁽²⁾
		Slave		–	–	1	μs
tfall	SSCK clock falling time	Master		–	–	1	tcyc ⁽²⁾
		Slave		–	–	1	μs
tsu	SSO, SSI data input setup time			100	–	–	ns
t _H	SSO, SSI data input hold time			1	–	–	tcyc ⁽²⁾
t _{LEAD}	$\overline{\text{SCS}}$ setup time	Slave		1tcyc + 50	–	–	ns
t _{LAG}	$\overline{\text{SCS}}$ hold time	Slave		1tcyc + 50	–	–	ns
t _{OD}	SSO, SSI data output delay time			–	–	1	tcyc ⁽²⁾
t _{SA}	SSI slave access time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5tcyc + 100	ns
			2.2 V ≤ V _{CC} < 2.7 V	–	–	1.5tcyc + 200	ns
t _{OR}	SSI slave out open time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5tcyc + 100	ns
			2.2 V ≤ V _{CC} < 2.7 V	–	–	1.5tcyc + 200	ns

NOTES:

1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. 1tcyc = 1/f₁(s)

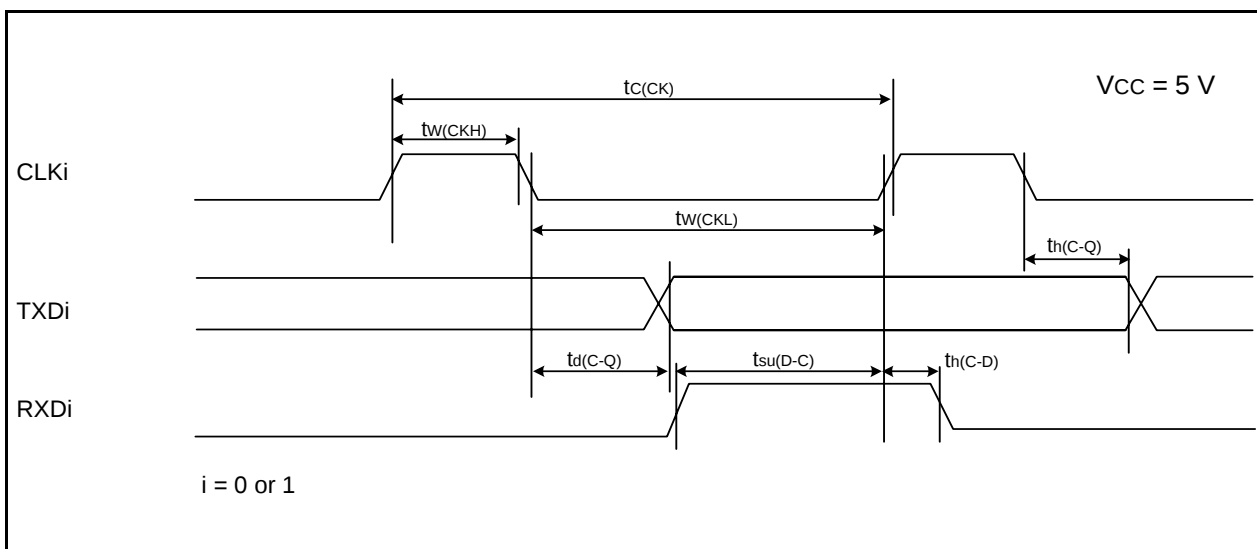
Table 5.16 Electrical Characteristics (2) [V_{CC} = 5 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit	
			Min.	Typ.	Max.		
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	17	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	10	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	μA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	130	300	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	μA

Table 5.20 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{w(CKH)}$	CLKi input "H" width	100	—	ns
$t_{w(CKL)}$	CLKi input "L" width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 or 1

**Figure 5.10 Serial Interface Timing Diagram when Vcc = 5 V****Table 5.21 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width	250 ⁽¹⁾	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width	250 ⁽²⁾	—	ns

NOTES:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

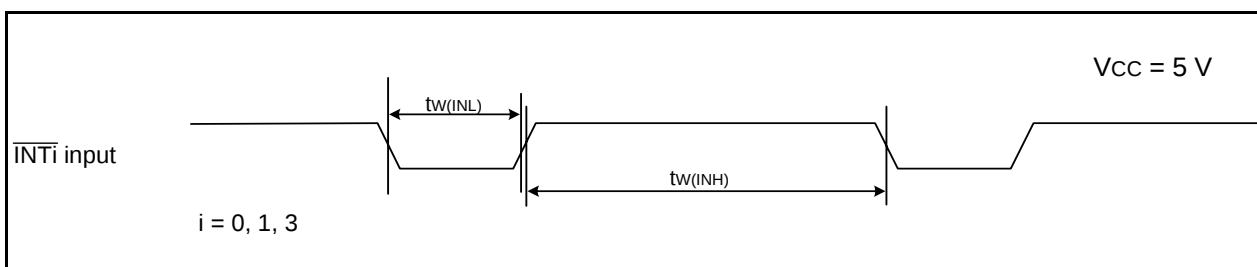
**Figure 5.11 External Interrupt $\overline{INTi}$ Input Timing Diagram when Vcc = 5 V**

Table 5.28 Electrical Characteristics (5) [V_{CC} = 2.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Except P1_0 to P1_7, XOUT	I _{OH} = -1 mA		V _{CC} - 0.5	—	V _{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I _{OH} = -2 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -1 mA	V _{CC} - 0.5	—	V _{CC}	V
		XOUT	Drive capacity HIGH	I _{OH} = -0.1 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -50 μA	V _{CC} - 0.5	—	V _{CC}	V
V _{OL}	Output "L" voltage	Except P1_0 to P1_7, XOUT	I _{OL} = 1 mA		—	—	0.5	V
		P1_0 to P1_7	Drive capacity HIGH	I _{OL} = 2 mA	—	—	0.5	V
			Drive capacity LOW	I _{OL} = 1 mA	—	—	0.5	V
		XOUT	Drive capacity HIGH	I _{OL} = 0.1 mA	—	—	0.5	V
			Drive capacity LOW	I _{OL} = 50 μA	—	—	0.5	V
V _{T+} -V _{T-}	Hysteresis	$\overline{\text{INT0}}, \overline{\text{INT1}}, \overline{\text{INT3}}, \overline{\text{KI0}}, \overline{\text{KI1}}, \overline{\text{KI2}}, \overline{\text{KI3}}, \overline{\text{TRAIO}}, \overline{\text{RXD0}}, \overline{\text{RXD1}}, \overline{\text{CLK0}}, \overline{\text{CLK1}}, \overline{\text{SSI}}, \overline{\text{SCL}}, \overline{\text{SDA}}, \overline{\text{SSO}}$			0.05	0.3	—	V
		$\overline{\text{RESET}}$			0.05	0.15	—	V
I _{IH}	Input "H" current		V _I = 2.2 V		—	—	4.0	μA
I _{IL}	Input "L" current		V _I = 0 V		—	—	-4.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V		100	200	600	kΩ
R _{FXIN}	Feedback resistance	XIN			—	5	—	MΩ
R _{FXCIN}	Feedback resistance	XCIN			—	35	—	MΩ
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

NOTE:

- V_{CC} = 2.2 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

5.2 J, K Version

Table 5.34 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V _{CC} /AV _{CC}	Supply voltage		-0.3 to 6.5	V
V _I	Input voltage		-0.3 to V _{CC} + 0.3	V
V _O	Output voltage		-0.3 to V _{CC} + 0.3	V
P _d	Power dissipation	-40 °C ≤ T _{opr} ≤ 85 °C	300	mW
		85 °C ≤ T _{opr} ≤ 125 °C	125	mW
T _{opr}	Operating ambient temperature		-40 to 85 (J version) / -40 to 125 (K version)	°C
T _{stg}	Storage temperature		-65 to 150	°C

Table 5.35 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V _{CC} /AV _{CC}	Supply voltage			2.7	–	5.5	V
V _{SS} /AV _{SS}	Supply voltage			–	0	–	V
V _{IH}	Input “H” voltage			0.8 V _{CC}	–	V _{CC}	V
V _{IL}	Input “L” voltage			0	–	0.2 V _{CC}	V
I _{OH} (sum)	Peak sum output “H” current	Sum of all pins I _{OH} (peak)		–	–	-60	mA
I _{OH} (peak)	Peak output “H” current			–	–	-10	mA
I _{OH} (avg)	Average output “H” current			–	–	-5	mA
I _{OL} (sum)	Peak sum output “L” currents	Sum of all pins I _{OL} (peak)		–	–	60	mA
I _{OL} (peak)	Peak output “L” currents			–	–	10	mA
I _{OL} (avg)	Average output “L” current			–	–	5	mA
f _(XIN)	XIN clock input oscillation frequency		3.0 V ≤ V _{CC} ≤ 5.5 V (other than K version)	0	–	20	MHz
			3.0 V ≤ V _{CC} ≤ 5.5 V (K version)	0	–	16	MHz
			2.7 V ≤ V _{CC} < 3.0 V	0	–	10	MHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V ≤ V _{CC} ≤ 5.5 V (other than K version)	0	–	20	MHz
			3.0 V ≤ V _{CC} ≤ 5.5 V (K version)	0	–	16	MHz
			2.7 V ≤ V _{CC} < 3.0 V	0	–	10	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected (other than K version)	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected	–	–	10	MHz

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.38 Flash Memory (Data flash Block A, Block B) Electrical Characteristics⁽⁴⁾

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	50	400	μs
—	Byte program time (program/erase endurance > 1,000 times)		—	65	—	μs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	9	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	97 + CPU clock × 6 cycles	μs
—	Interval from erase start/restart until following suspend request		650	—	—	μs
—	Interval from program start/restart until following suspend request		0	—	—	ns
—	Time from suspend until program/erase restart		—	—	3 + CPU clock × 4 cycles	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		2.7	—	5.5	V
—	Program, erase temperature		-40	—	85 ⁽⁸⁾	°C
—	Data hold time ⁽⁹⁾	Ambient temperature = 55°C	20	—	—	year

NOTES:

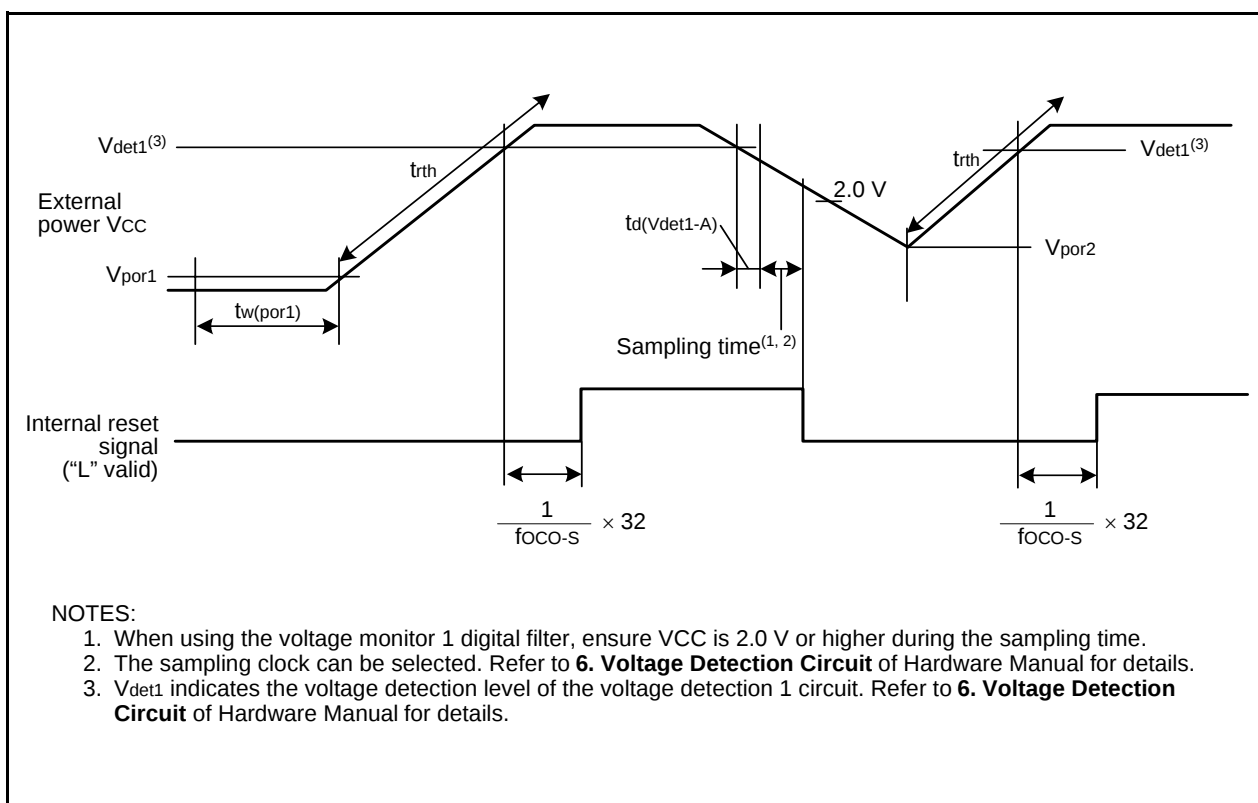
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. 125°C for K version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.41 Power-on Reset Circuit, Voltage Monitor 1 Reset Electrical Characteristics⁽³⁾

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{por1}	Power-on reset valid voltage ⁽⁴⁾		–	–	0.1	V
V _{por2}	Power-on reset or voltage monitor 1 reset valid voltage		0	–	V _{det1}	V
tr _{th}	External power V _{CC} rise gradient	V _{CC} ≤ 3.6 V	20 ⁽²⁾	–	–	mV/msec
		V _{CC} > 3.6 V	20 ⁽²⁾	–	2,000	mV/msec

NOTES:

1. The measurement condition is T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. This condition (the minimum value of external power V_{CC} rise gradient) does not apply if V_{por2} ≥ 1.0 V.
3. To use the power-on reset function, enable voltage monitor 1 reset by setting the LVD1ON bit in the OFS register to 0, the VW1C0 and VW1C6 bits in the VW1C register to 1 respectively, and the VCA26 bit in the VCA2 register to 1.
4. t_{w(por1)} indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain t_{w(por1)} for 30 s or more if -20°C ≤ T_{opr} ≤ 125°C, maintain t_{w(por1)} for 3,000 s or more if -40°C ≤ T_{opr} < -20°C.

**Figure 5.22 Reset Circuit Electrical Characteristics**

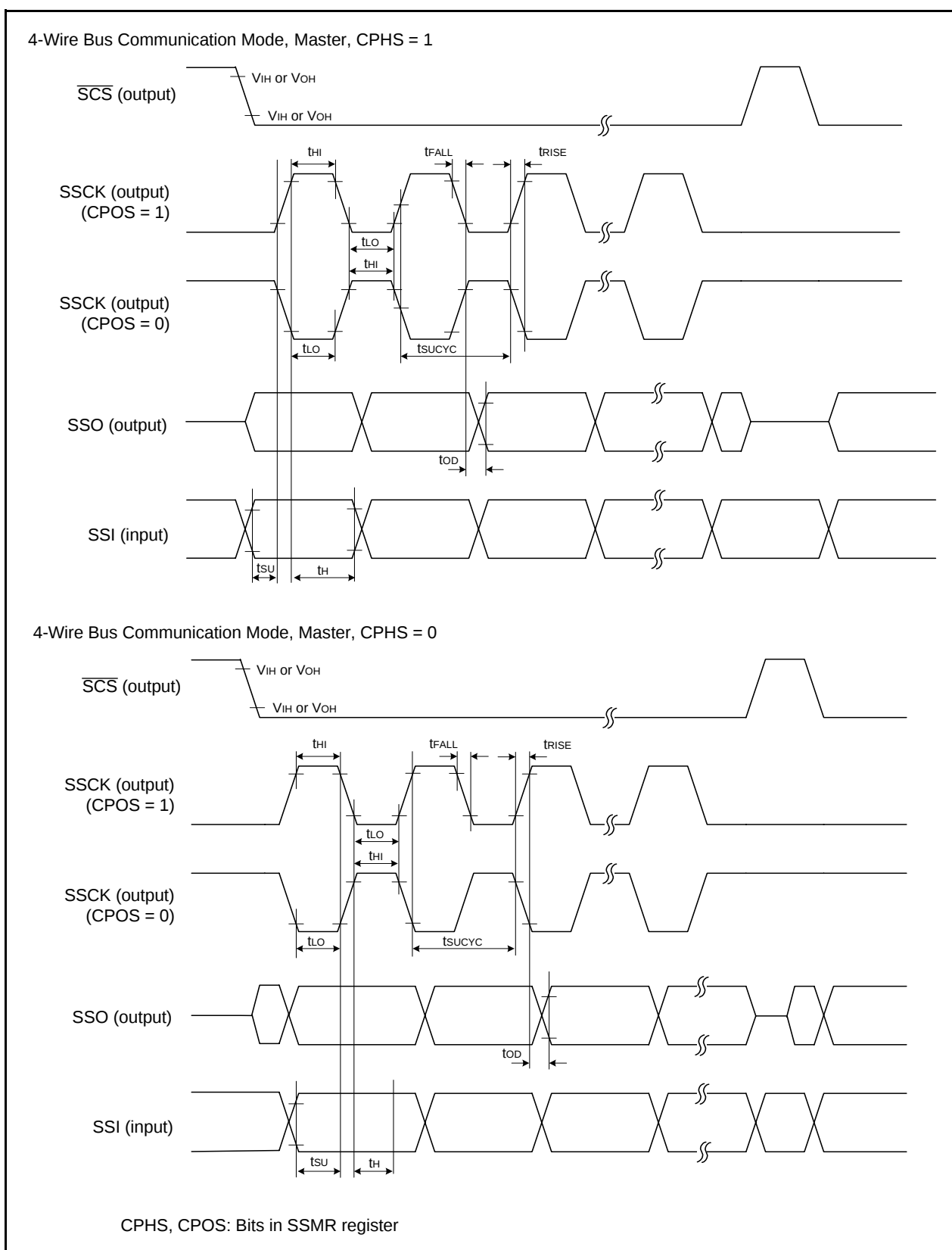


Figure 5.23 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

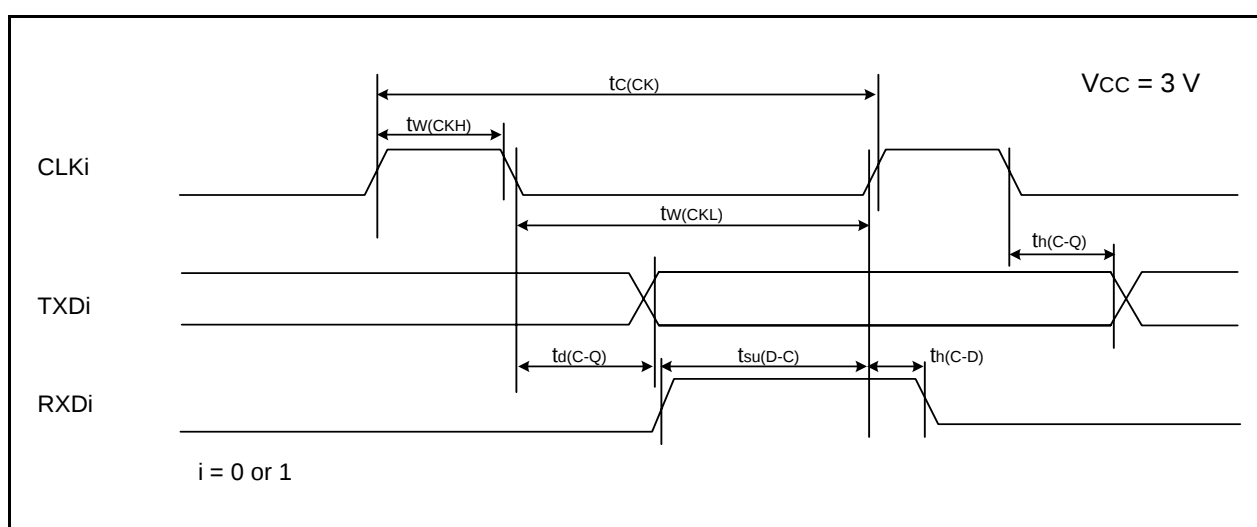
Table 5.48 Electrical Characteristics (2) [V_{CC} = 5 V]
(T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	17	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz (J version) Low-speed on-chip oscillator on = 125 kHz No division	–	10	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz (J version) Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	75	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	60	μA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.8	3.0	μA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.2	–	μA
			XIN clock off, Topr = 125°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	4.0	–	μA

Table 5.57 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	—	ns
$t_{w(CKH)}$	CLKi input "H" width	150	—	ns
$t_{w(CKL)}$	CLKi Input "L" width	150	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	70	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

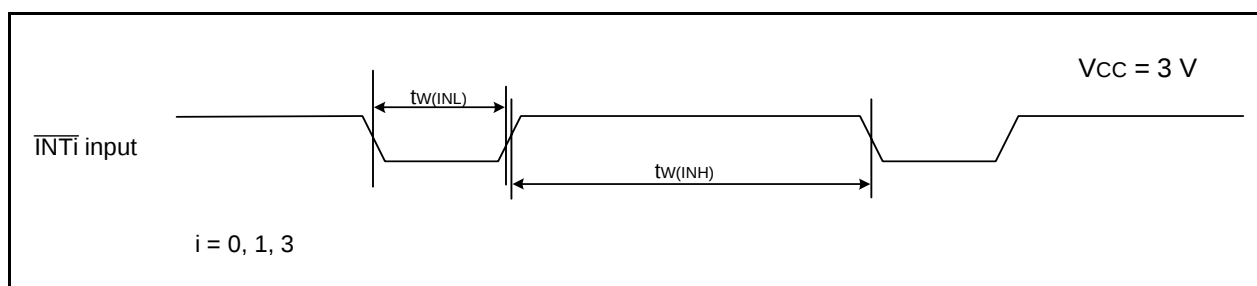
i = 0 or 1

**Figure 5.33 Serial Interface Timing Diagram when Vcc = 3 V****Table 5.58 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width	380 ⁽¹⁾	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width	380 ⁽²⁾	—	ns

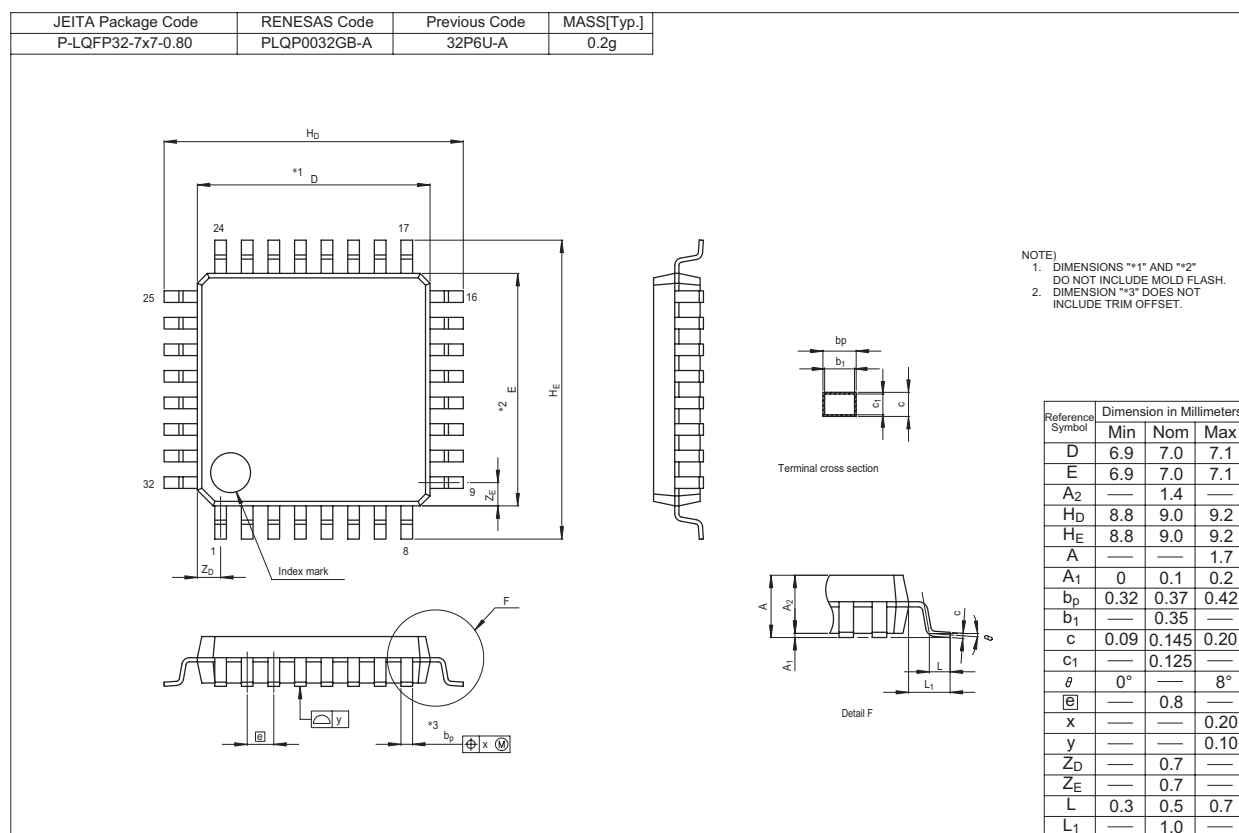
NOTES:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

**Figure 5.34 External Interrupt $\overline{INTi}$ Input Timing Diagram when Vcc = 3 V**

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.



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